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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <small>(Use as many sheets as necessary)</small>	
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Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Geusic, Joseph
Group Art Unit	Unknown
Examiner Name	Unknown
10-2	
Sheet 2 of 2	Attorney Docket No: 303.390US4

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EXAMINER *Elie V. Haldane*

DATE CONSIDERED 08/05/2005

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Substitute for Form 1449A PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		Complete if Known	
		Application Number	Unknown
		Filing Date	Even Date Herewith
		First Named Inventor	Geusic, Joseph
		Group Art Unit	Unknown
Examiner Name	Unknown		
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